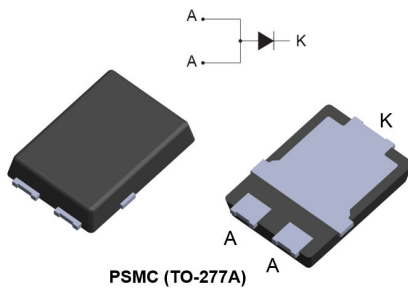


100 V - 10 A power Schottky trench diode



Features

- ST trench patented process
- High junction temperature capability
- Low forward voltage drop
- Low recovery charges
- Reduces conduction, reverse and switching losses
- Avalanche tested
- Flat packages
- ECOPACK2 compliant

Applications

- DC/DC converter
- LED lighting
- Flyback topology
- Auxiliary power supply
- Switch mode power supply (SMPS)

Description

This 10 A, 100 V rectifier is based on ST trench technology that achieves the best-in-class V_F/I_R trade-off for a given silicon surface.

Integrated in flat and space-saving packages, this STPST10H100 trench rectifier is intended to be used in high frequency miniature switched mode power supplies. It is also an ideal candidate for auxiliary power supply in telecom, server, or smart metering. ST trench rectifiers are adapted to freewheeling, OR-ring or reverse polarity protection applications, and can be the perfect companion device to our transistors, drivers, or ST VIPer products.

Product label



Product status link

[STPST10H100](#)

Product summary

$I_{F(AV)}$	10 A
V_{RRM}	100 V
T_j (max.)	175 °C
V_F (typ.)	0.565 V

1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified, with 2 anode terminals short-circuited)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		100	V
$I_{F(AV)}$	Average forward current, $\delta = 0.5$ square wave	$T_c = 155\text{ °C}^{(1)}$	10	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	235	A
I_{AS}	Single pulse avalanche current ⁽²⁾	$T_j = 25\text{ °C}$, $L = 300\text{ }\mu\text{H}$, $V_{DD} = 15\text{ V}$	14	A
T_{stg}	Storage temperature range		-65 to +175	°C
T_j	Maximum operating junction temperature ⁽³⁾		+175	°C

1. Value based on $R_{th(j-c)}(max.)$.
2. Please refer to [Figure 1](#) and [Figure 2](#) for the unclamped inductive switching test circuit, and waveform.
3. $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameter

Symbol	Parameter		Typ. value	Unit
$R_{th(j-c)}$	Junction to case	PSMC (TO-277)	1.25	°C/W

For more information, please refer to the following application note:

- [AN5088](#): Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 125\text{ °C}$	$V_R = 70\text{ V}$	-	2	6.4	mA
		$T_j = 25\text{ °C}$	$V_R = 100\text{ V}$	-		26	μA
		$T_j = 125\text{ °C}$		-	4	13.5	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 5\text{ A}$	-	0.535	0.590	V
		$T_j = 125\text{ °C}$		-	0.460	0.520	
		$T_j = 25\text{ °C}$	$I_F = 10\text{ A}$	-	0.635	0.700	
		$T_j = 125\text{ °C}$		-	0.565	0.620	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 0.42 \times I_{F(AV)} + 0.020 \times I_F^2_{(RMS)}$$

For more information, please refer to the following application notes related to the power losses :

- [AN604](#): Calculation of conduction losses in a power rectifier
- [AN4021](#): Calculation of reverse losses on a power diode

Figure 1. Current and voltage waveforms for avalanche energy test across D.U.T (device under test)

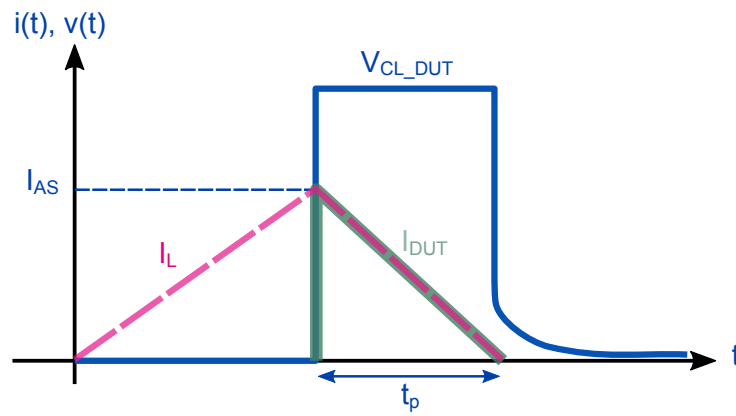
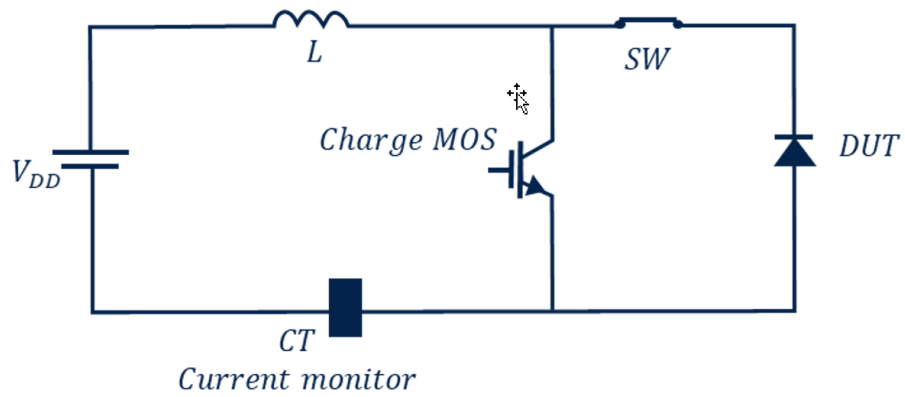


Figure 2. Unclamped inductive switching test circuit



$$E_{AS} = \frac{1}{2} \times L \times I_{AS}^2 \times \left(\frac{V_{CLDUT}}{V_{CLDUT} - V_{DD}} \right) \cong \frac{1}{2} \times L \times I_{AS}^2$$

$$t_p = \left(\frac{L \times I_{AS}}{V_{CLDUT} - V_{DD}} \right)$$

1.1 Characteristics (curves)

Figure 3. Average forward current versus case temperature ($\delta = 0.5$)

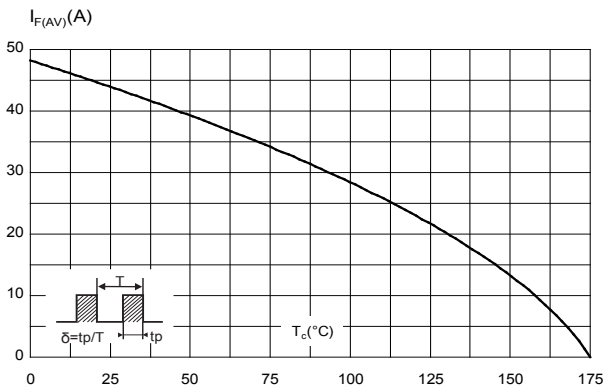


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

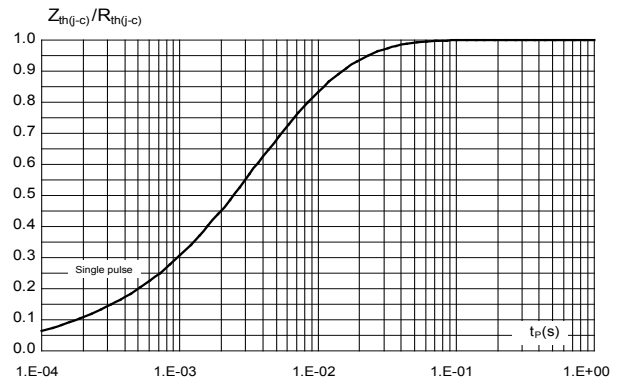


Figure 5. Reverse leakage current versus reverse voltage applied (typical values)

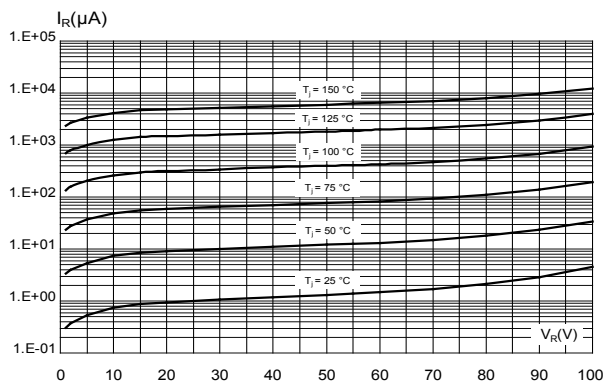


Figure 6. Junction capacitance versus reverse voltage applied (typical values)

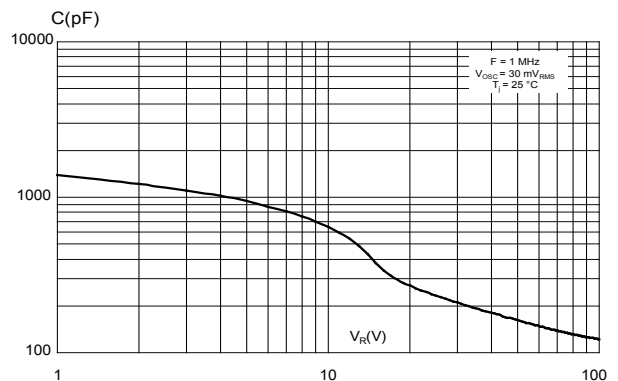


Figure 7. Forward voltage drop versus forward current (typical values)

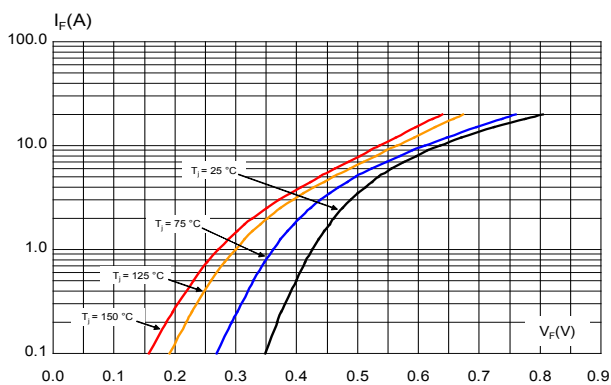
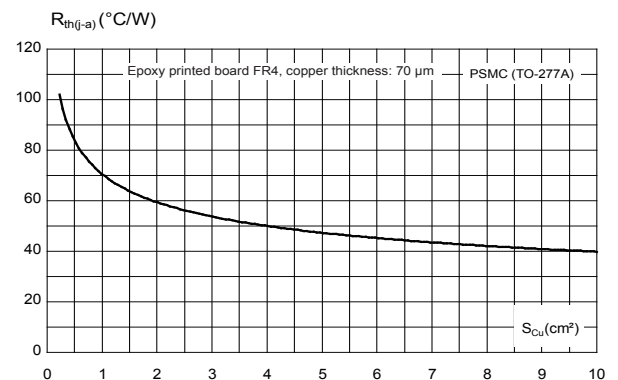


Figure 8. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4, $e_{\text{Cu}} = 70 \mu\text{m}$)



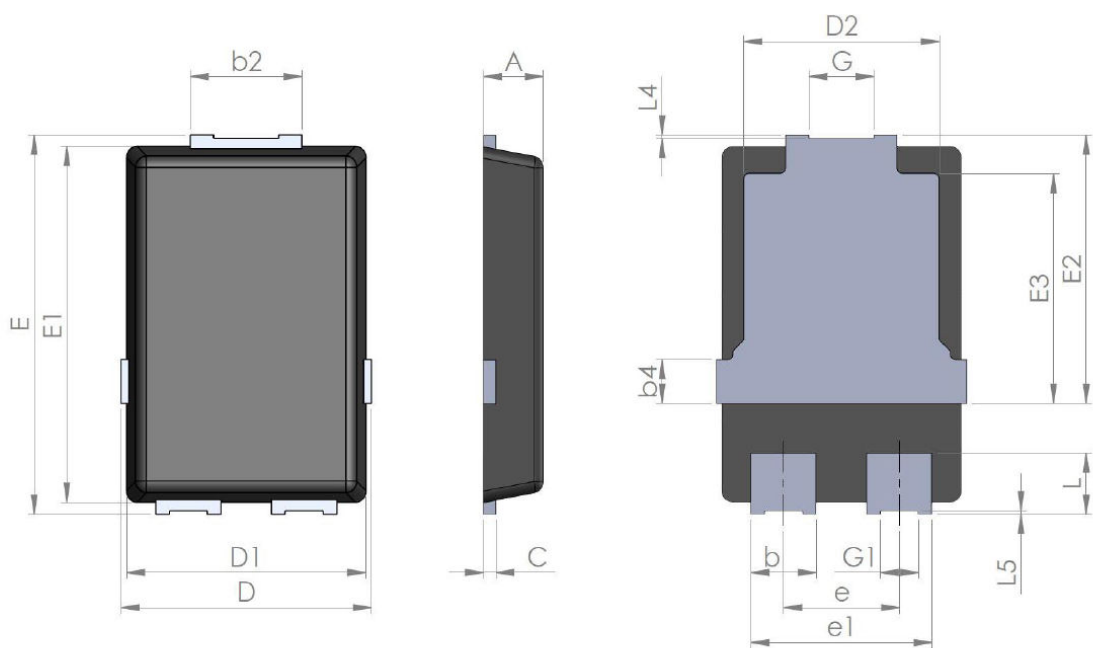
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 PSMC (TO-277A) package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

Figure 9. PSMC (TO-277A) package outline

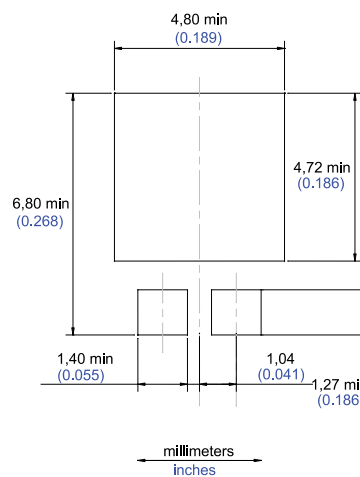


Note: This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 4. PSMC (TO-277A) package mechanical data

Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.00	1.10	1.20	0.039	0.043	0.047
b	1.05	1.20	1.35	0.041	0.047	0.053
b2	1.90	2.05	2.20	0.075	0.081	0.087
b4		0.75			0.029	
C	0.15	0.23	0.40	0.006	0.009	0.016
D	4.45	4.60	4.75	0.175	0.181	0.187
D1	4.25	4.40	4.45	0.167	0.173	0.175
D2	3.40	3.60	3.70	0.134	0.142	0.146
E	6.35	6.50	6.65	0.250	0.256	0.262
E1	6.05	6.10	6.15	0.238	0.240	0.242
E2	4.50	4.60	4.70	0.177	0.181	0.185
E3		3.94			1.55	
e		2.13			0.084	
e1		3.33			0.131	
G		1.20			0.047	
G1		0.70			0.027	
L	0.90	1.05	1.24	0.035	0.041	0.049
L4	0.02			0.0008		
L5	0.02			0.0008		

Figure 10. PSMC (TO-277A) package footprint in mm (in inches)



Note: For package and tape orientation, reel and inner box dimensions and tape outline please check [TN1173](#).

3 Ordering information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPST10H100SF	T10H1	PSMC (TO-277A)	90 mg	6000	Tape and reel

Revision history

Table 6. Document revision history

Date	Version	Changes
25-Jan-2021	1	Initial release.
01-Jun-2023	2	Updated Table 1 .

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